

# ZXMN2F30FH 20V SOT23 N-channel enhancement mode MOSFET

## **Summary**

V <sub>(BR)DSS</sub>	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)
20	0.045 @ V <sub>GS</sub> = 4.5V	4.9
	0.065 @ V <sub>GS</sub> = 2.5V	4.1

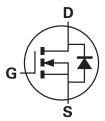


### **Description**

This new generation Trench MOSFET from Zetex features low onresistance achievable with low (2.5V) gate drive.

### **Features**

- · Low on-resistance
- · 2.5V gate drive capability
- · SOT23 package

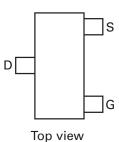


### **Applications**

- Buck/Boost DC-DC Converters
- · Load switching and SMPS
- · Charging applications in portable equipment
- Motor Control
- · LED Lighting

## **Ordering information**

DEVICE	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN2F30FHTA	7	8	3000



### **Device marking**

**KNC** 

## **Absolute maximum ratings**

Parameter	Symbol	Limit	Unit
Drain source voltage	V <sub>DSS</sub>	20	V
Gate source voltage	V <sub>GS</sub>	±12	V
Continous Drain Current @ V <sub>GS</sub> =4.5; T <sub>A</sub> =25°C <sup>(b)</sup> @ V <sub>GS</sub> =4.5; T <sub>A</sub> =70°C <sup>(b)</sup> @ V <sub>GS</sub> =4.5; T <sub>A</sub> =25°C <sup>(a)</sup>	I <sub>D</sub>	4.9 4.0 4.1	A A A
Pulsed drain current <sup>(c)</sup>	I <sub>DM</sub>	22.6	Α
Continuous source current (body diode)(b)	I <sub>S</sub>	1.6	Α
Pulsed source current (body diode)(c)	I <sub>SM</sub>	22.6	Α
Power dissipation at T <sub>A</sub> =25°C <sup>(a)</sup>	P <sub>D</sub>	0.96	W
Linear derating factor		7.6	mW/°C
Power dissipation at T <sub>A</sub> =25°C <sup>(b)</sup>	P <sub>D</sub>	1.4	W
Linear derating factor		11.2	mW/°C
Operating and storage temperature range	T <sub>j</sub> , T <sub>stg</sub>	-55 to 150	°C

### Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\Theta JA}$	131	°C/W
Junction to ambient <sup>(b)</sup>	$R_{\Theta JA}$	89	°C/W
Junction to Lead <sup>(d)</sup>	$R_{\Theta JL}$	68	°C/W

### NOTES:

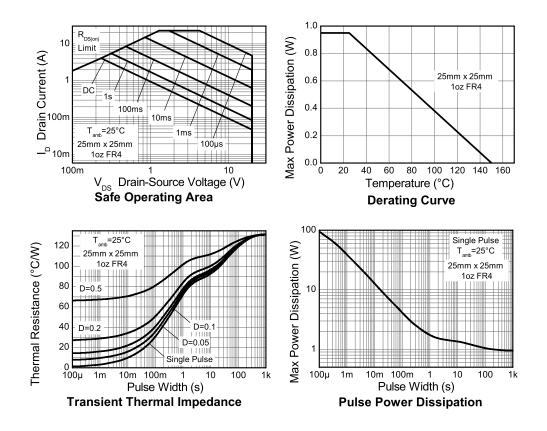
<sup>(</sup>a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

<sup>(</sup>b) For a device surface mounted on FR4 PCB measured at  $t \le 5$  sec.

<sup>(</sup>c) Repetitive rating -  $25mm \times 25mm \text{ FR4 PCB}$ , D=0.02, pulse width  $300\mu s$  - pulse width limited by maximum junction temperature.

<sup>(</sup>d) Thermal resistance from junction to solder-point (at the end of the drain lead).

### Thermal characteristics



# Electrical characteristics (at T<sub>amb</sub> = 25°C unless otherwise stated)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Static						•	
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	20			V	$I_{D}$ = 250 $\mu$ A, $V_{GS}$ =0V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			1	μΑ	V <sub>DS</sub> = 20V, V <sub>GS</sub> =0V	
Gate-Body Leakage	I <sub>GSS</sub>			100	nA	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	0.6	0.9	1.5	V	$I_D=250\mu A, V_{DS}=V_{GS}$	
Static Drain-Source	R <sub>DS(on)</sub>			0.045	Ω	$V_{GS}$ = 4.5V, $I_{D}$ = 2.5A	
On-State Resistance (*)				0.065	Ω	$V_{GS}$ = 2.5V, $I_{D}$ = 2.0A	
Forward Transconductance <sup>(*)(†)</sup>	g <sub>fs</sub>		8.6		S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 3A	
Dynamic (†)							
Input Capacitance	C <sub>iss</sub>		452		pF	.,	
Output Capacitance	C <sub>oss</sub>		102		рF	V <sub>DS</sub> = 10V, V <sub>GS</sub> =0V f=1MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>		58		pF	- 1- 11/11/2	
Switching (‡)(†)							
Turn-On-Delay Time	t <sub>d(on)</sub>		2.9		ns		
Rise Time	t <sub>r</sub>		5.6		ns	V <sub>DD</sub> = 10V, V <sub>GS</sub> = 4.5V I <sub>D</sub> = 1A	
Turn-Off Delay Time	t <sub>d(off)</sub>		19.4		ns	$R_G \approx 6.0\Omega$	
Fall Time	t <sub>f</sub>		10.2		ns		
Total Gate Charge	$Q_g$		4.8		nC	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 4.5V	
Gate-Source Charge	$Q_{gs}$		1		nC	I <sub>D</sub> = 3.5A	
Gate Drain Charge	Q <sub>gd</sub>		1.2		nC		
Source-drain diode			1	1		1	
Diode Forward Voltage <sup>(*)</sup>	$V_{SD}$		0.75	1.2	V	I <sub>S</sub> = 1.25A, V <sub>GS</sub> =0V	

#### NOTES

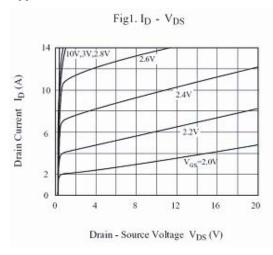
Downloaded from Elcodis.com electronic components distributor

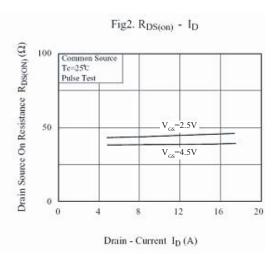
<sup>(\*)</sup> Measured under pulsed conditions. Pulse width  $\leq 300 \mu s;$  duty cycle  $\leq\!\!2\%.$ 

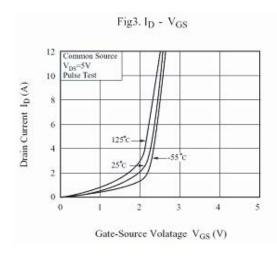
<sup>(†)</sup> For design aid only, not subject to production testing.

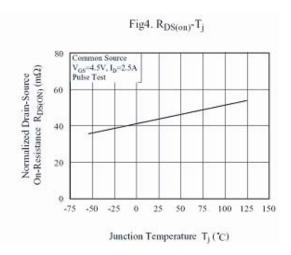
<sup>(‡)</sup> Switching characteristics are independent of operating junction temperature.

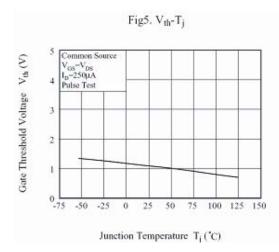
### **Typical characteristics**

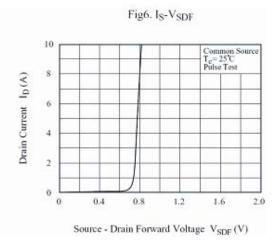




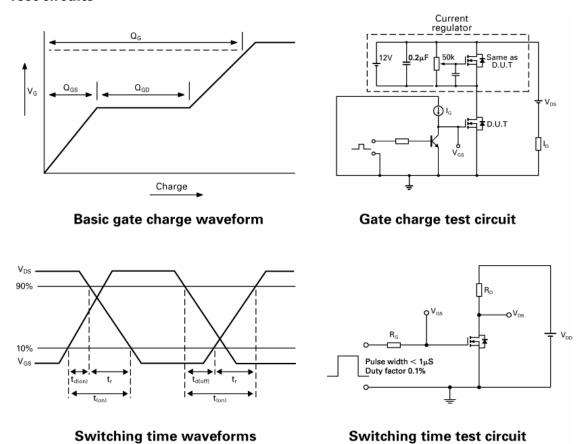




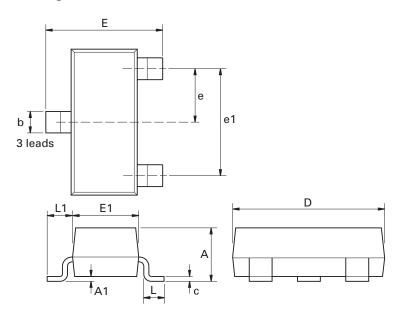




### **Test circuits**



# Package outline - SOT23



Dim.	Millin	neters	Inc	hes	Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
Α	-	1.12	-	0.044	e1	1.90	NOM	0.075	NOM
A1	0.01	0.10	0.0004	0.004	Е	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
С	0.085	0.20	0.003	0.008	L	0.25	0.60	0.0098	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
е	0.95	NOM	0.037	NOM	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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